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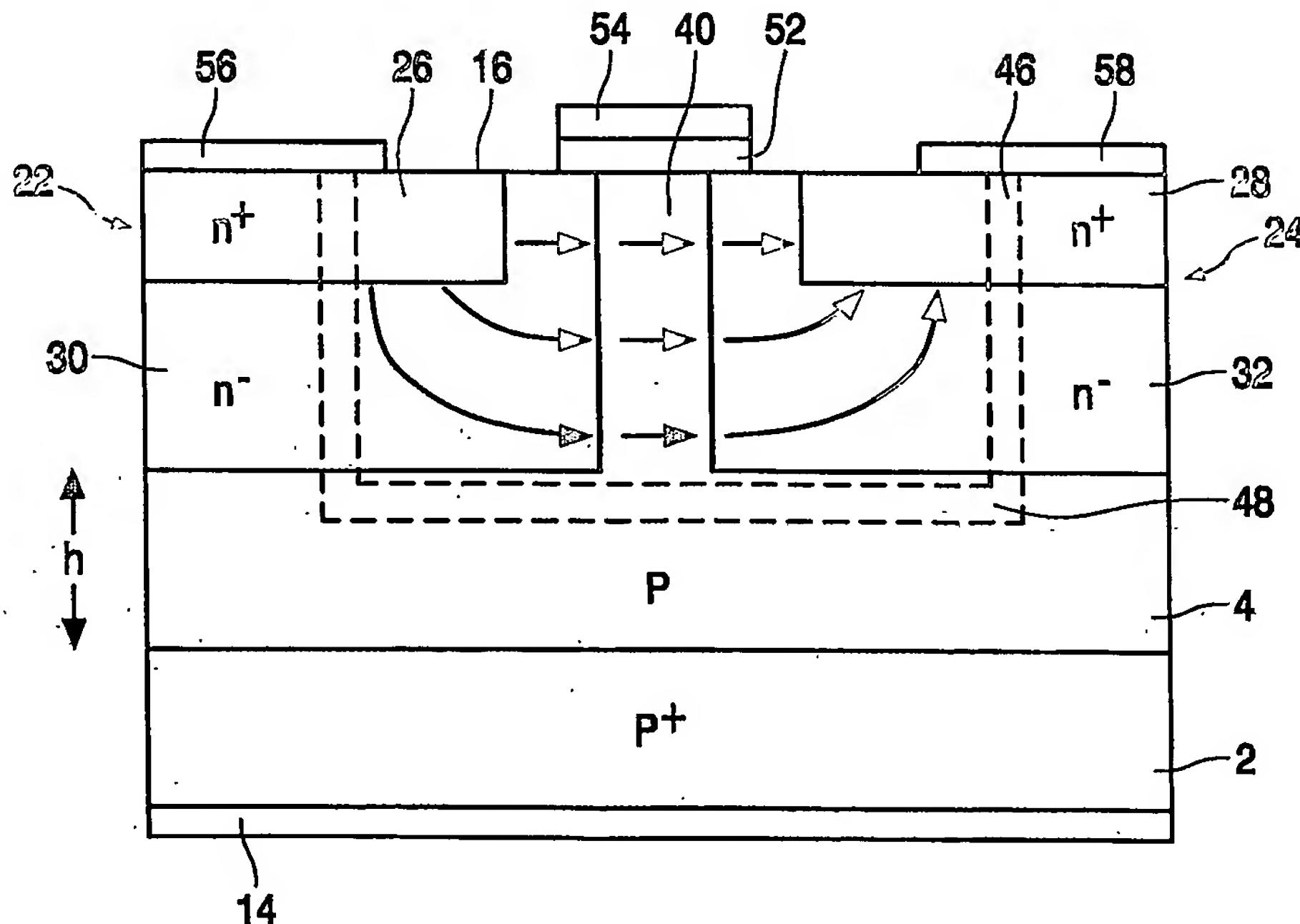
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(54) Title: TRENCH MOS STRUCTURE



(57) Abstract: A semiconductor device has a trench (42) adjacent to a cell (18). The cell includes source and drain contact regions (26, 28), and a central body (40) of opposite conductivity type. The device is bidirectional and controls current in either direction with a relatively low on-resistance. Preferred embodiments include potential plates (56) that act together with source and drain drift regions (30, 32) to create a RESURF effect.

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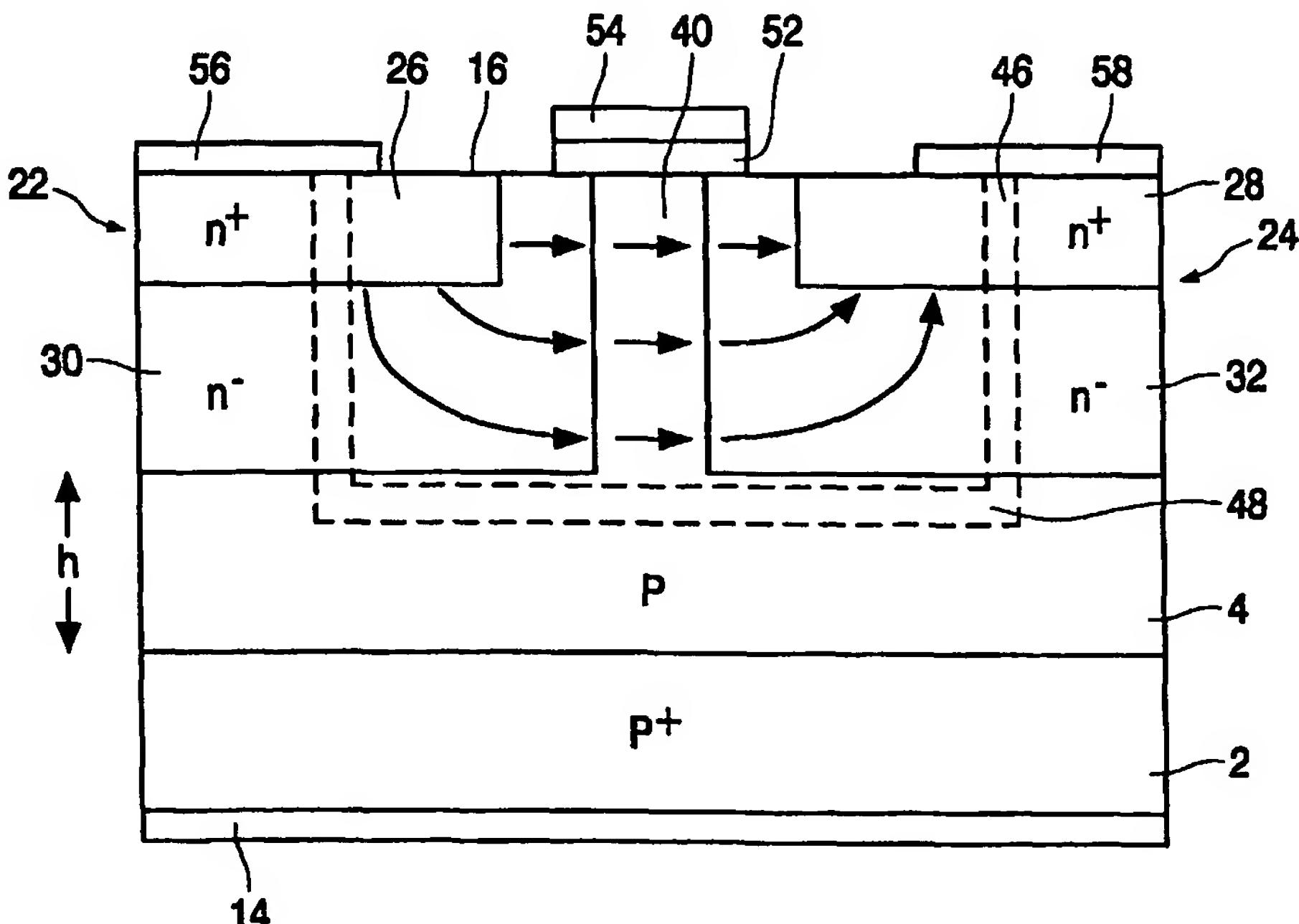
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